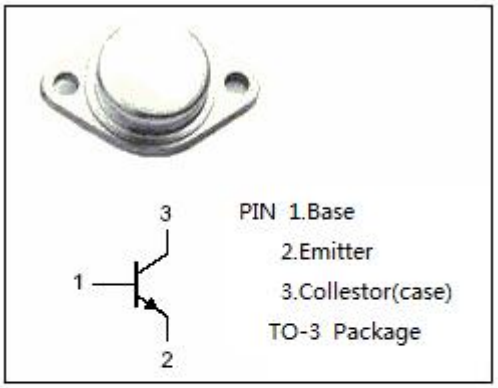
isc Silicon NPN Power Transistor — BUS98A

DESCRIPTION

- High Voltage Capability
- High Current Capability
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

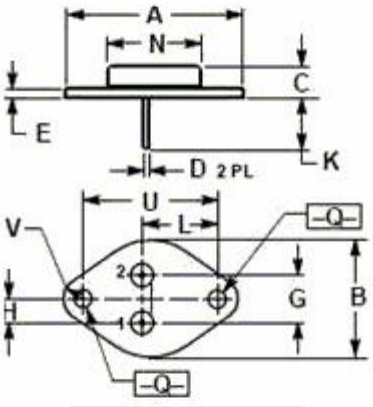


APPLICATIONS

Designed for high-voltage,high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line-operated swtchmode applications

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage (V_{BE}= -1.5V)	1000	V
V_{CEO}	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	30	A
I_{CM}	Collector Current-Peak	60	A
I_B	Base Current-Continuous	10	A
I_{BM}	Base Current-peak	30	A
P_C	Collector Power Dissipation @T_C=25℃	250	W
T_j	Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.0	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA ; I_B= 0	450		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	7		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 16A; I_B= 3.2A I_C= 16A; I_B= 3.2A;T_C= 100℃		1.5 2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 24A ;I_B=5A		5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C=16A; I_B= 3.2A I_C= 16A; I_B= 3.2A;T_C= 100℃		1.6 1.6	V
I_{CBO}	Collector Base Cutoff Current	V_{CB}=1000V; I_E= 0 V_{CB}=1000V; I_E= 0;T_C=125℃		0.4 4	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0		0.1	mA
h_{FE}	DC Current Gain	I_C= 16A ; V_{CE}= 5V	8		